Substitute form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/617,843
				Filing Date	July 11, 2003
				First Named Inventor	Saxler
				Group Art Unit	2823
(use as many sheets as necessary)				Examiner Name	Fernando L. Toledo
Sheet	A1	of	A1	Attorney Docket Number	5308-248

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Examiner Initials*	Cite No.	U.S. Patent Document Number	U.S. Patent Document Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY

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Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
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FLT	8.	United States Patent Application entitled "Methods of Fabricating Nitride-Based Transistors Having Regrown Ohmic Contact Regions and Nitride-Based Transistors Having Regrown Ohmic Contact Regions," Serial No. 10/849,617, filed May 20, 2004 (Attorney Docket No. 5308-413).	
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Examiner Signature		Date Considered	9/16/04

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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Attorney Docket Number: 5308-248	Serial No.: 10/617,843
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